TOSHIBA TC7S86F/FU

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC7S86F, TC7S86FU

EXCLUSIVE OR GATE

The TC7S86 is a high speed C²MOS EXCLUSIVE OR GATE fabricated with silicon gate C²MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the C²MOS low power dissipation.

Input and output buffers are provided which offer high noise immunity and stable output. All inputs are equipped with protection circuits against static dischage or transient excess voltage.

Output current are 1/2 compared to TC74HC series models.

FEATURES

High Speed	$t_{pd} = 10$ ns (Typ.) at
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• Low Power Dissipation $I_{CC} = 1\mu A$ (Max.) at $Ta = 25^{\circ}C$

High Noise Immunity V_{NIH} = V_{NIL}

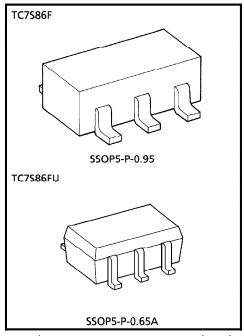
= 28% V_{CC} (Min.)

Output Drive Capability 5 LSTTL Loads

• Symmetrical Output Impedance ... $|I_{OH}| = I_{OL}$ = 2mA (Min.)

Balanced Propagation Delays t_{pLH}≒t_{pHL}

Wide Operating Voltage Range ... V_{CC} (opr) = 2~6V



Weight SSOP5-P-0.95 : 0.016g (Typ.) SSOP5-P-0.65A : 0.006g (Typ.)

MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage Range	V _C C	-0.5~7	V
DC Input Voltage	V _{IN}	-0.5~V _{CC} +0.5	٧
DC Output Voltage	Vout	−0.5~V _{CC} + 0.5	<
Input Diode Current	ΙΚ	± 20	mA
Output Diode Current	lok	± 20	mA
DC Output Current	IOUT	± 12.5	mΑ
DC V _{CC} /Ground Current	lcc	± 25	mΑ
Power Dissipation	PD	200	mW
Storage Temperature	T _{stg}	- 65∼150	°C
Lead Temperature (10s)	ΤL	260	°C

TRUTH TABLE

Α	В	>
Н	Н	L
L	Н	Н
Н	L	Н
L	L	L

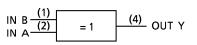
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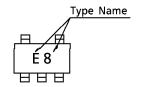
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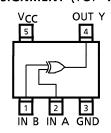
LOGIC DIAGRAM

MARKING

PIN ASSIGNMENT (TOP VIEW)







RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	۷сс	2~6	V
Input Voltage	VIN	0~V _{CC}	V
Output Voltage	VOUT	0~V _{CC}	V
Operating Temperature	T _{opr}	- 40~85	°C
		$0 \sim 1000 \text{ (V}_{CC} = 2.0\text{V)}$	
Input Rise and Fall Time	t _r , t _f	$0 \sim 500 \ (V_{CC} = 4.5V)$	ns
		$0 \sim 400 \ (V_{CC} = 6.0V)$	

DC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC SYMBOL		TEST CONDITION VCC		Т	a = 25°	C.	Ta = -4	UNIT		
				Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High-Level					1.5	_	_	1.5	_	
Input Voltage	VIH		_	4.5	3.15	 	—	3.15	—	V
put voitage				6.0	4.2		<u> </u>	4.2	_	
Low-Level				2.0	—	—	0.5	—	0.5	
Input Voltage	V _{IL}		_	4.5	—	—	1.35	—	1.35	V
Input voltage				6.0			1.8		1.8	
				2.0	1.9	2.0	—	1.9	—	
High-Level	VOH	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -20\mu A$	4.5	4.4	4.5	—	4.4	—	
				6.0	5.9	6.0		5.9	_	V
Output Voltage			$I_{OH} = -2mA$	4.5	4.18	4.31	—	4.13	_	
			$I_{OH} = -2.6 mA$	6.0	5.68	5.80	—	5.63		
		V _{IN} = V _{IH} or V _{IL}		2.0	l —	0.0	0.1	_	0.1	
Laure Laurel			I _{OL} = 20μA	4.5	l —	0.0	0.1	—	0.1	
Low-Level	V _{OL}			6.0	l —	0.0	0.1	—	0.1	V
Output Voltage			I _{OL} = 2mA	4.5	_	0.17	0.26	_	0.33	
			$I_{OL} = 2.6 mA$	6.0	 —	0.18	0.26	—	0.33	
Input Leakage Current	IN	V _{IN} = V _{CC} or GND		6.0	_	_	±0.1	_	± 1.0	μΑ
Quiescent Supply Current	lcc	V _{IN} = V _{CC} or GND		6.0	_	_	1.0	_	10.0	μ A

Output currents are 1/2 compared to TC74HC series models.

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AC ELECTRICAL CHARACTERISTICS ($C_L = 15pF$, $V_{CC} = 5V$, Ta = 25°C, Input $t_r = t_f = 6ns$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	Т	UNIT		
CHARACTERISTIC	STIVIBUL	TEST CONDITION		TYP.	MAX.	UNII
Output Transition	tTLH			1	Q	
Time	tTHL	_	_	-	0	nc
Propagation Delay	t _{pLH}			10	17	ns
Time	t _{pHL}			10	''	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50pF$, Input $t_r = t_f = 6ns$)

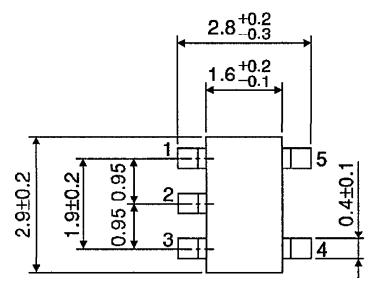
CHARACTERISTIC	SYMBOL	TEST CONDITION		Ta = 25°C			Ta = -4	UNIT	
CHARACTERISTIC	STIVIBOL	TEST CONDITION	Vcc	MIN.	TYP.	MAX.	MIN.	MAX.	CIVIT
Output Transition t _{TLH} t _{THL}	4		2.0	_	50	125	_	155	
	_	4.5	 —	14	25	_	31		
		6.0	l —	12	21	—	26	ne	
Brancastica Dalay 4	4	_	2.0	_	48	100	_	125	ns
	ropagation Delay t _{pLH}		4.5	 	12	20	—	25	
Time t _{pHL}		6.0	_	9	17	—	21		
Input Capacitance	C _{IN}	_		_	5	10	_	10	рF
Power Dissipation Capacitance	C _{PD}	(Note 1)		_	18	_		_	pF

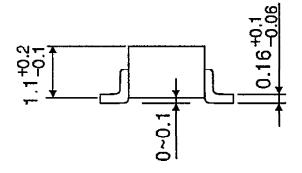
Note 1: CPD is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation. ICC (opr) = CPD·VCC·fIN + ICC

OUTLINE DRAWING

SSOP5-P-0.95



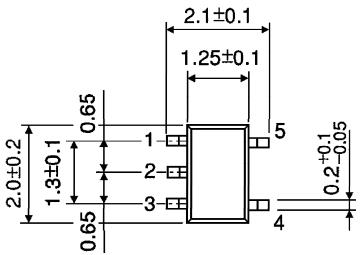




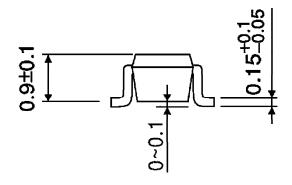
Weight: 0.016g (Typ.)

OUTLINE DRAWING

SSOP5-P-0.65A



Unit: mm



Weight: 0.006g (Typ.)